RF Power Field Effect Transistors

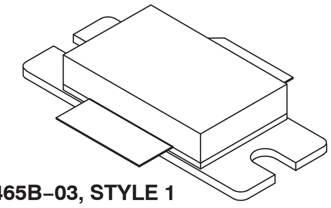
N−Channel Enhancement−Mode Lateral MOSFETs

MRF9200LR3
MRF9200LSR3

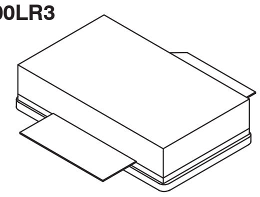
Designed for broadband commercial and industrial applications with frequencies to 1000 MHz. The high gain and broadband performance of these devices make them ideal for large−signal, common−source amplifier applications in 26 volt base station equipment.

- Typical Single−Carrier N−CDMA Performance @ 880 MHz: V_{DD} = 26 Volts, I_{DQ} = 2400 mA, P_{out} = 40 Watts Avg., IS−95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13). Channel Bandwidth = 1.2288 MHz. Peak/Avg. Ratio = 9.8 dB @ 0.01% Probability on CCDF.
  Power Gain — 17.5 dB
  Drain Efficiency — 25%
  ACPR @ 750 kHz Offset — −46.5 dBc @ 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 880 MHz, 40 Watts N−CDMA Output Power
- Characterized with Series Equivalent Large−Signal Impedance Parameters
- Internally Matched, Controlled Q, for Ease of Use
- Integrated ESD Protection
- Low Gold Plating Thickness on Leads, 40μ″ Nominal.
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

880 MHz, 40 W AVG., 26 V
SINGLE N−CDMA
LATERAL N−CHANNEL
RF POWER MOSFETs



CASE 465B−03, STYLE 1
NI−880
MRF9200LR3



CASE 465C−02, STYLE 1
NI−880S
MRF9200LSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain−Source Voltage	V_{DSS}	−0.5, +65	Vdc
Gate−Source Voltage	V_{GS}	−0.5, +15	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	625 3.6	W W/°C
Storage Temperature Range	T_{stg}	− 65 to +150	°C
Operating Junction Temperature	T_J	200	°C
CW Operation Case Temperature 60°C Case Temperature 80°C	CW	 200 160	W

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 60°C, 200 W CW Case Temperature 80°C, 40 W CW	$R_{\theta JC}$	 0.28 0.34	°C/W

1. MTTF calculator available at http://www.freescale.com/rf. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.freescale.com/rf. Select Documentation/Application Notes − AN1955.

NOTE − **CAUTION** − MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

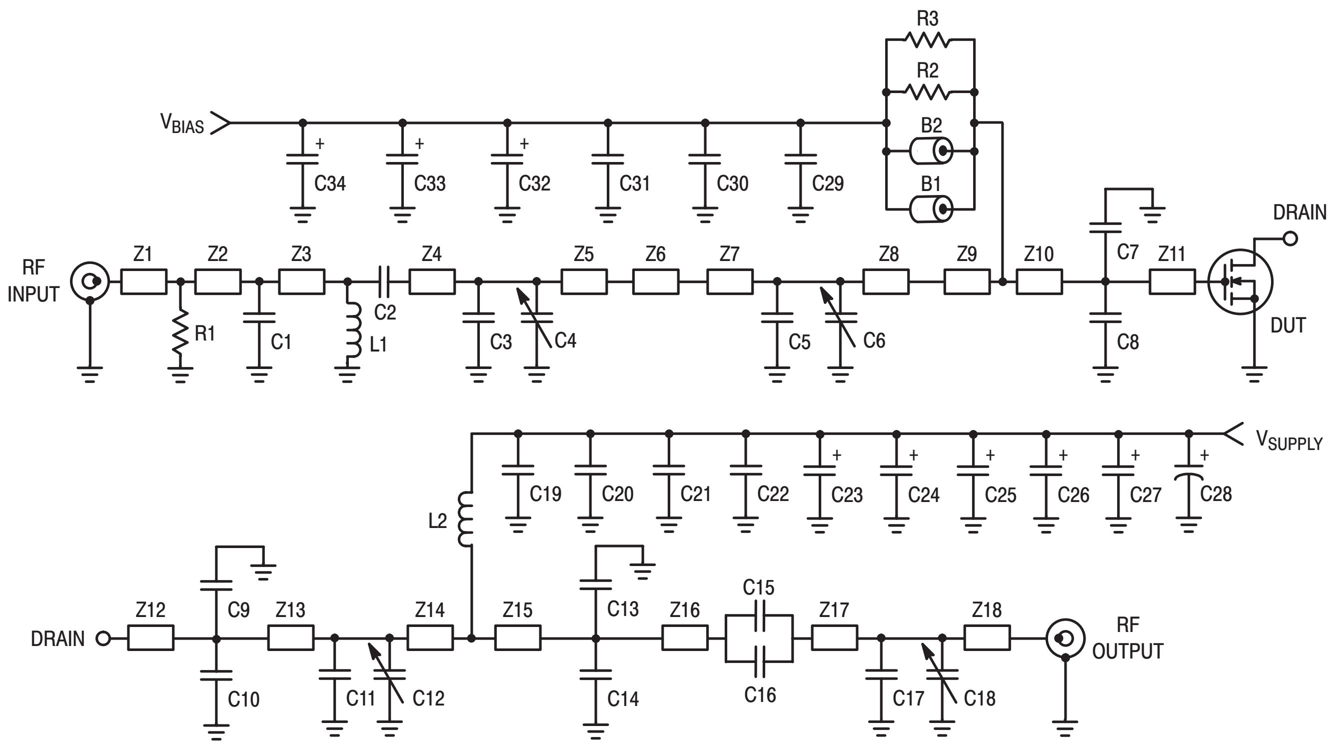
Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model (per JESD22−A114)	1C (Minimum)
Machine Model (per EIA/JESD22−A115)	B (Minimum)
Charge Device Model (per JESD22−C101)	IV (Minimum)

Table 4. Electrical Characteristics (T_C = 25°C unless otherwise noted)

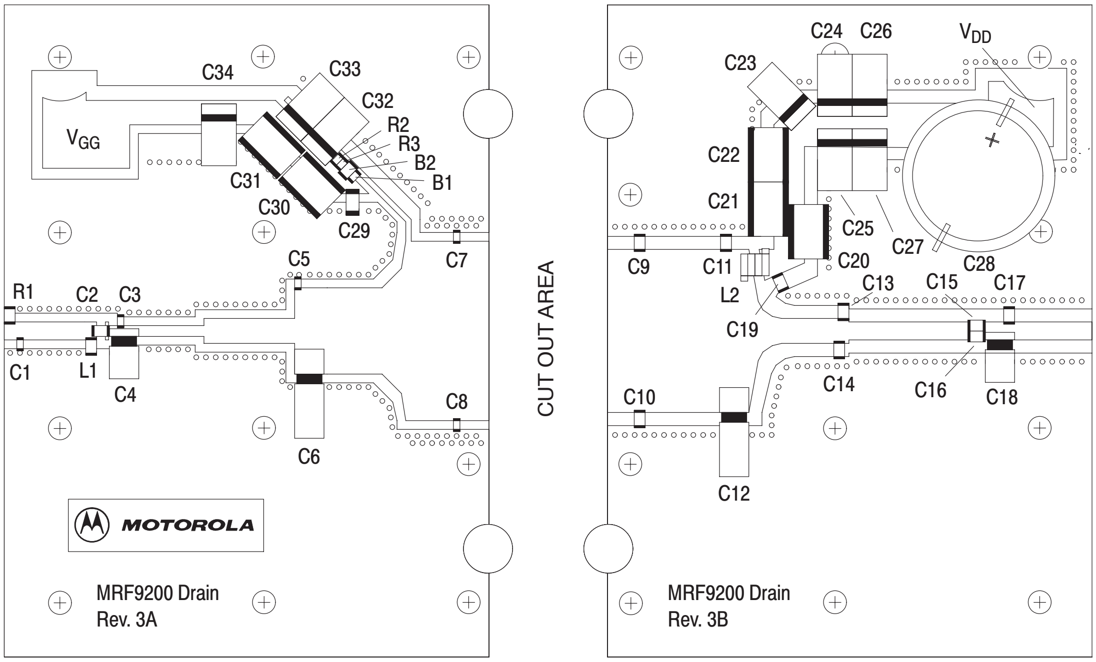
Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current (V_{DS} = 65 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current (V_{DS} = 26 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	1	μAdc
Gate−Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 100 μAdc)	$V_{GS(th)}$	1.5	2.7	3.5	Vdc
Gate Quiescent Voltage (V_{DS} = 26 Vdc, I_D = 2400 mAdc)	$V_{GS(Q)}$	3	3.7	4.5	Vdc
Drain−Source On−Voltage (V_{GS} = 10 Vdc, I_D = 6.0 Adc)	$V_{DS(on)}$	—	0.25	0.4	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 6.7 Adc)	g_{fs}	—	8.8	—	S
Dynamic Characteristics (1)					
Reverse Transfer Capacitance (V_{DS} = 26 Vdc ± 30 mV(rms)ac @ 1 MHz, V_{GS} = 0 Vdc)	C_{rss}	—	2.5	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system) V_{DD} = 26 Vdc, I_{DQ} = 2400 mA, P_{out} = 40 W Avg. N−CDMA, f = 880 MHz, Single−Carrier N−CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @ ±750 kHz Offset. Peak/Avg. Ratio = 9.8 dB @ 0.01% Probability on CCDF.					
Power Gain	G_{ps}	16	17.5	—	dB
Drain Efficiency	η_D	22	25	—	%
Adjacent Channel Power Ratio	ACPR	—	−46.5	−45	dBc
Input Return Loss	IRL	—	−13	−9	dB

1. Part is internally matched both on input and output.



Z1	0.015″ x 0.083″ Microstrip	Z8	0.335″ x 0.397″ Microstrip	Z14	0.197″ x 0.750″ x 0.111″ Taper
Z2	0.048″ x 0.083″ Microstrip	Z9	0.134″ x 0.825″ x 0.090″ Taper	Z15	0.331″ x 0.115″ Microstrip
Z3	0.352″ x 0.083″ Microstrip	Z10	0.209″ x 0.825″ Microstrip	Z16	0.557″ x 0.830″ Microstrip
Z4	0.086″ x 0.050″ Microstrip	Z11	0.148″ x 0.825″ Microstrip	Z17	0.078″ x 0.830″ Microstrip
Z5	0.367″ x 0.050″ Microstrip	Z12	0.148″ x 0.750″ Microstrip	Z18	0.414″ x 0.750″ Microstrip
Z6	0.417″ x 0.115″ Microstrip	Z13	0.435″ x 0.750″ Microstrip	PCB	Arlon, 0.030″, ε_r = 2.56
Z7	0.068″ x 0.397″ Microstrip				

Figure 1. MRF9200LR3(SR3) Test Circuit Schematic



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF9200LR3(SR3) Test Circuit Component Layout

Table 5. MRF9200LR3(SR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	RF Bead, Surface Mount (0603)	2506033007Y0	Fair−Rite
B2	RF Bead, Surface Mount (0805)	2508051107Y0	Fair−Rite
C1	2.2 pF Chip Capacitor (0603)	GQM1885C2A2R2CB01B	Murata
C2, C19	47 pF Chip Capacitors (0805)	GQM2195C1H470JB01B	Murata
C3	2.0 pF Chip Capacitor (0603)	GQM1885C2A2R0BB01B	Murata
C4, C18	0.4−2.5 pF Variable Capacitors	27283PC	Gigatronics
C5	8.2 pF Chip Capacitor (0603)	GQM1885C1H8R2DB01B	Murata
C6, C12	0.8−8.0 pF Variable Capacitors	27291SL	Gigatronics
C7, C8	12 pF Chip Capacitors (0603)	GQM1885C1H120JB01B	Murata
C9, C10	10 pF Chip Capacitors (0805)	GQM2195C2A100JB01B	Murata
C11	5.1 pF Chip Capacitor (0805)	GQM2195C2A5R1DB01B	Murata
C13	3.3 pF Chip Capacitor (0805)	GQM2195C2A3R3CB01B	Murata
C14, C17	1.5 pF Chip Capacitors (0805)	GQM2195C2A1R5CB01B	Murata
C15, C16	22 pF Chip Capacitors (0805)	GQM2195C1H220JB01B	Murata
C20	0.56 μF Chip Capacitor (1825)	C1825C564J5RAC	Kemet
C21, C22, C31	2.2 μF Chip Capacitors (1825)	C1825C225J5RAC	Kemet
C23	10 μF, 50 V Tantalum Chip Capacitor	522Z−050/100MTRE	Tecate
C24, C25, C26, C27	22 μF, 35 V Tantalum Chip Capacitors	T491X226K035AS	Kemet
C28	330 μF, 63 V Electrolytic Capacitor	NACZF331M100V (18X22)	Nippon
C29	10 μF Chip Capacitor (1206)	GRM31MF51A106ZA01B	Murata
C30	0.01 μF Chip Capacitor (1825)	C1825C103J1RAC	Kemet
C32, C33	22 μF, 25 V Tantalum Chip Capacitors	ECS−T1ED226R	Panasonic TE series
C34	47 μF, 16 V Tantalum Chip Capacitor	T491D476K016AS	Kemet
L1	22 nH Chip Inductor (0805)	L0805220JEW	AVX
L2	8 nH Inductor	A03T−5	CoilCraft
R1	510 Ω, 1/10 W Chip Resistor (0805)		Dale/Vishay
R2, R3	11 Ω, 1/8 W Chip Resistors (1206)		Dale/Vishay

TYPICAL CHARACTERISTICS

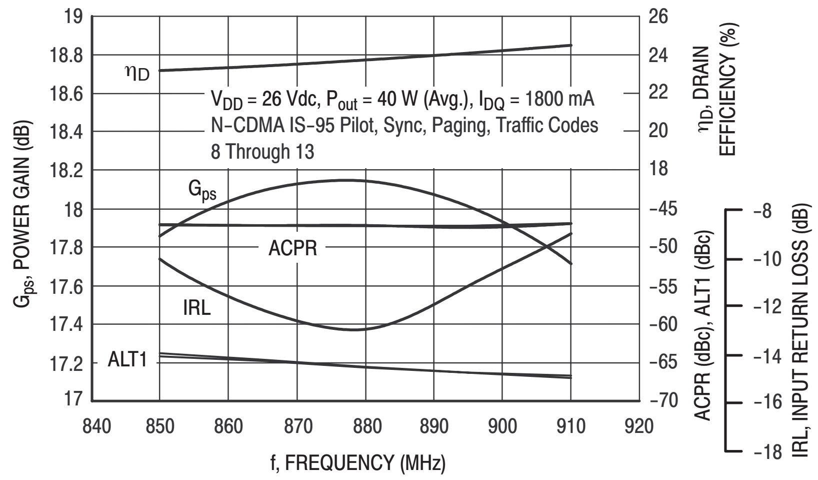


Figure 3. Single−Carrier N−CDMA Broadband Performance @ P_{out} = 40 Watts Avg.

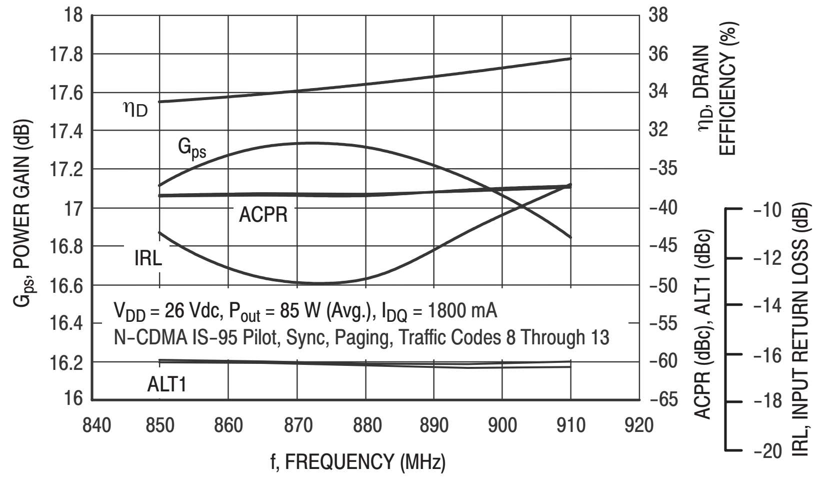


Figure 4. Single−Carrier N−CDMA Broadband Performance @ P_{out} = 85 Watts Avg.

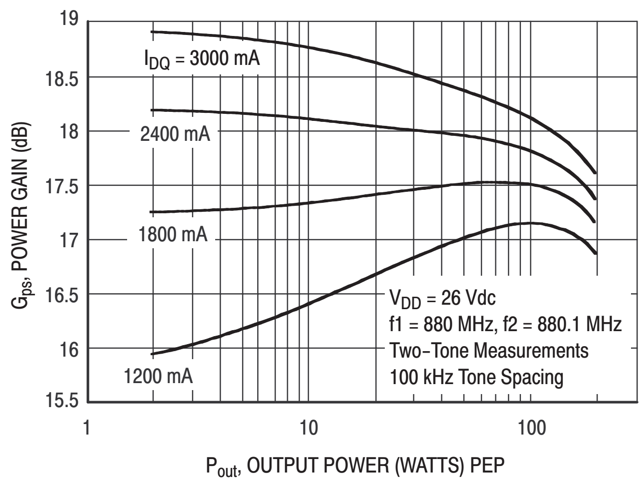


Figure 5. Two−Tone Power Gain versus Output Power

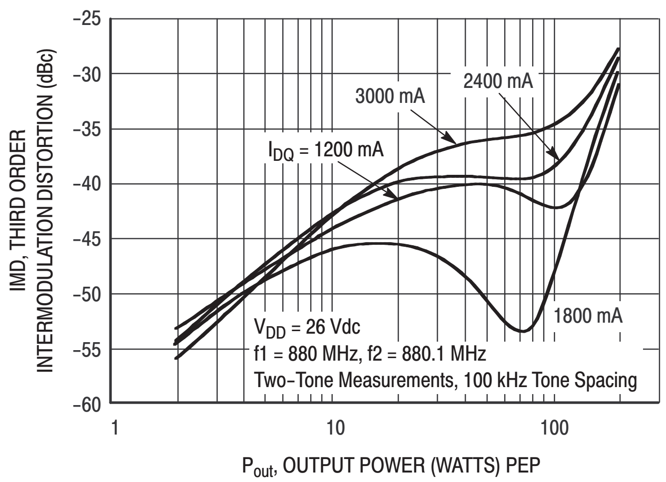


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

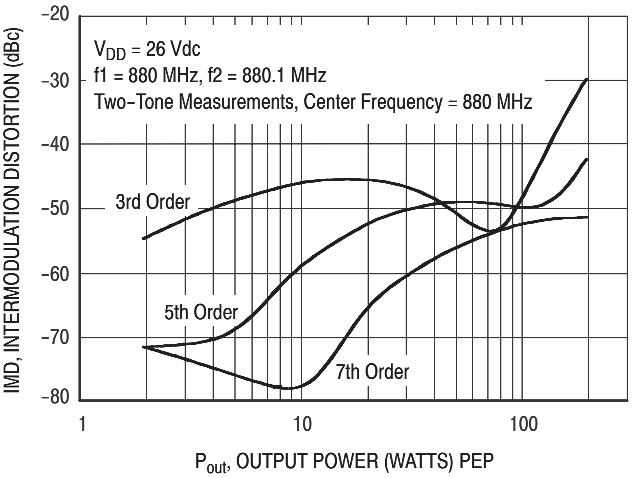


Figure 7. Intermodulation Distortion Products versus Output Power

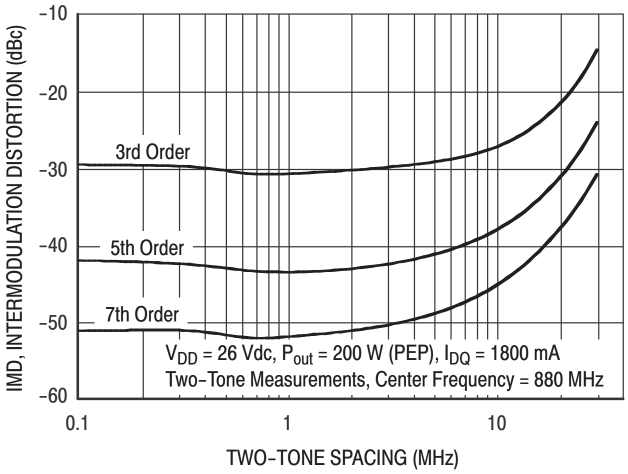


Figure 8. Intermodulation Distortion Products versus Tone Spacing

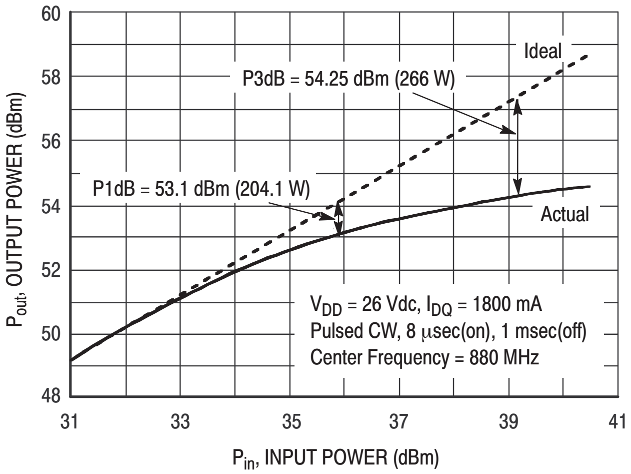


Figure 9. Pulse CW Output Power versus Input Power

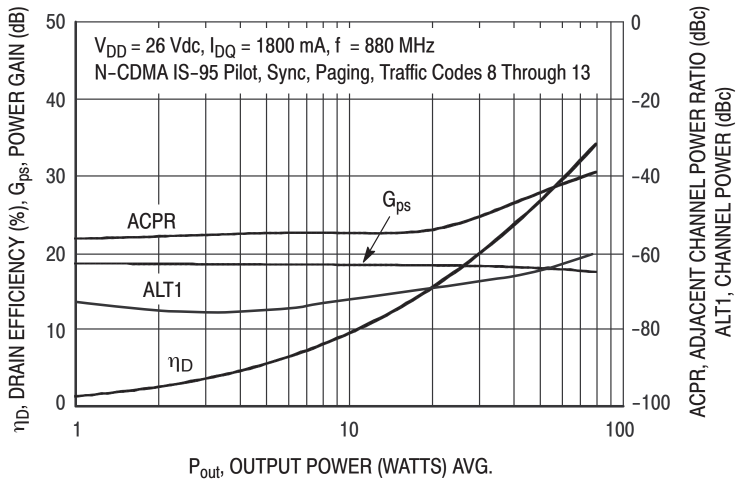


Figure 10. Single−Carrier N−CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power

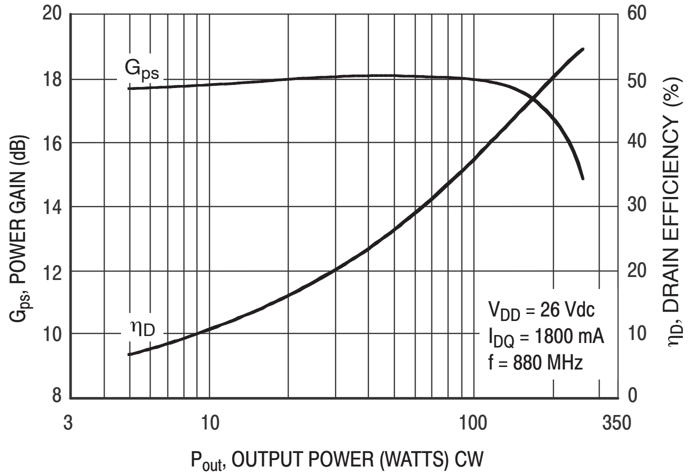


Figure 11. Power Gain and Drain Efficiency versus CW Output Power

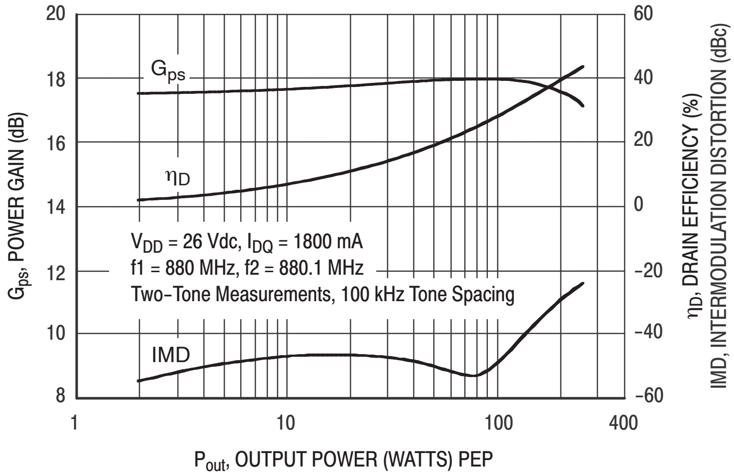


Figure 12. Power Gain, Efficiency and IMD versus Output Power

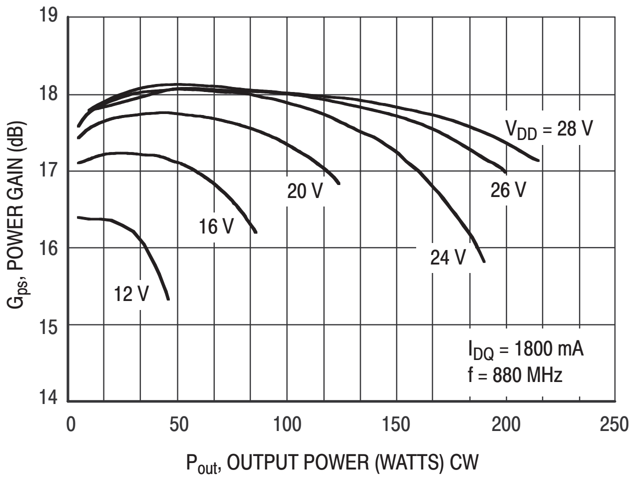
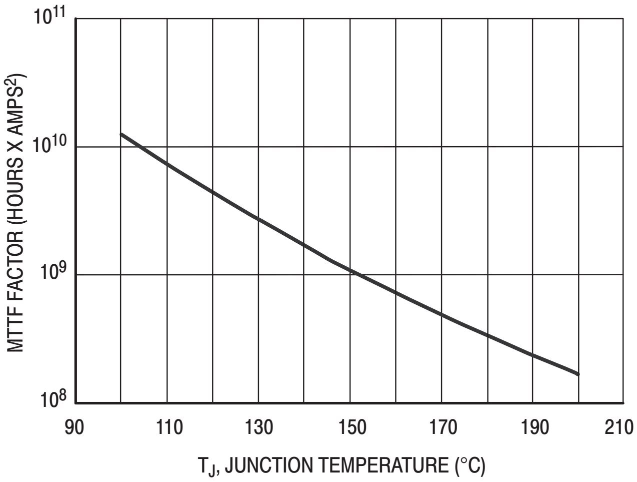


Figure 13. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours x ampere^2 drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by $I_D{}^2$ for MTTF in a particular application.

Figure 14. MTTF Factor versus Junction Temperature

TYPICAL CHARACTERISTICS
N−CDMA TEST SIGNAL

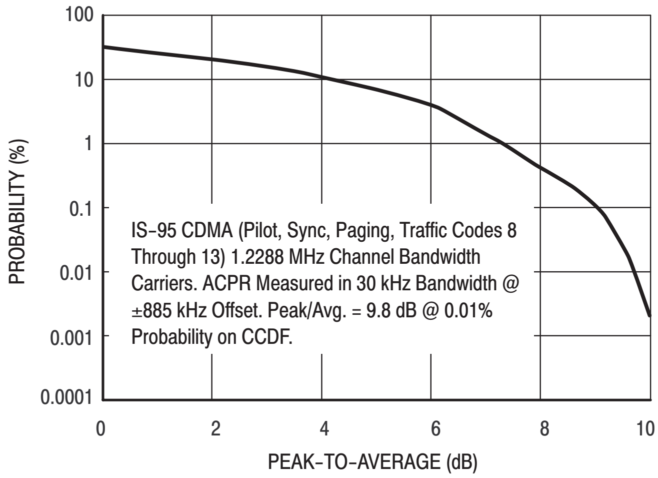


Figure 15. Single−Carrier CCDF N−CDMA

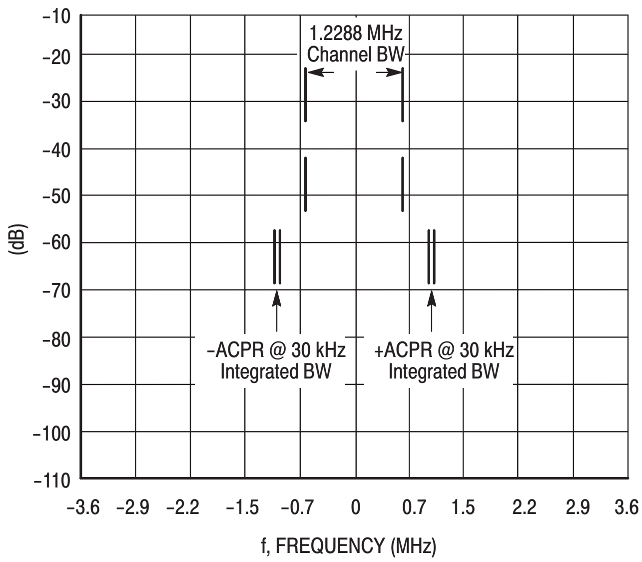
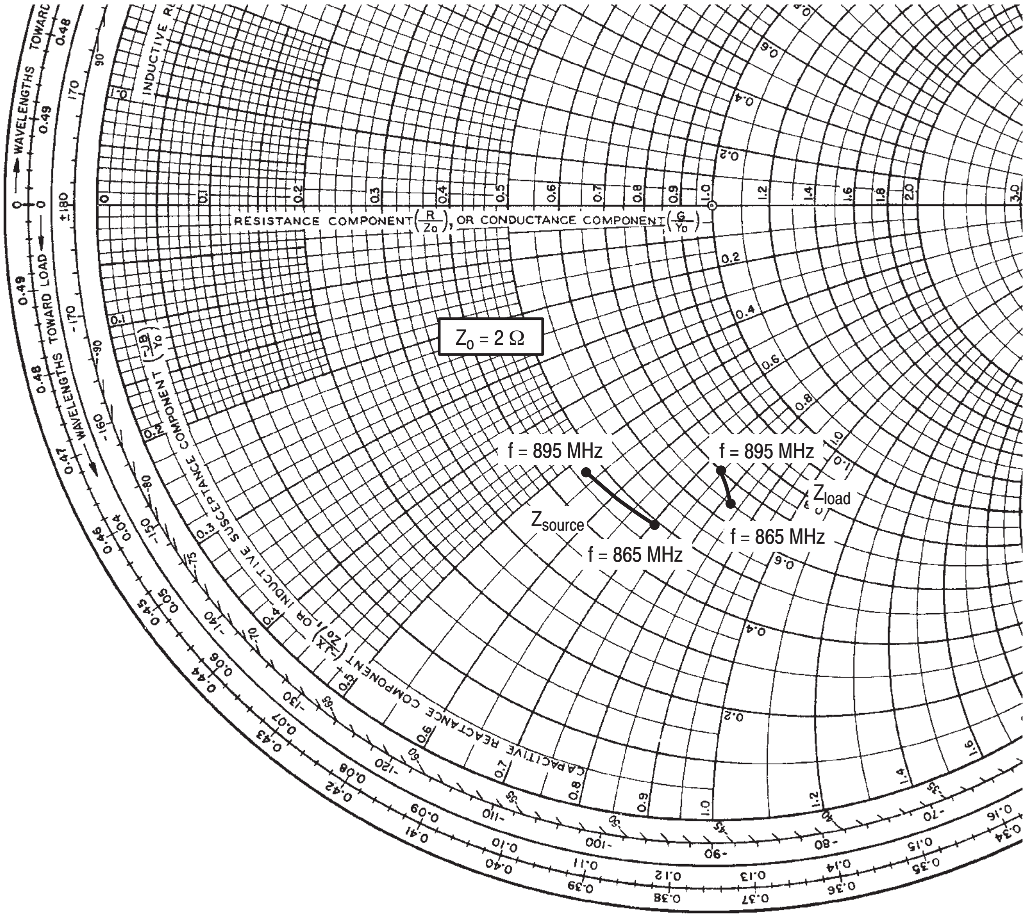


Figure 16. Single−Carrier N−CDMA Spectrum



V_{DD} = 26 Vdc, I_{DQ} = 2400 mA, P_{out} = 40 W Avg. N-CDMA

f MHz	Z_{source} Ω	Z_{load} Ω
865	0.98 – j1.41	1.30 – j1.66
880	0.96 – j1.23	1.36 – j1.58
895	0.94 – j1.06	1.40 – j1.50

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

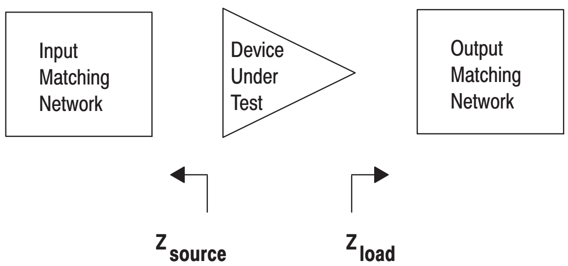
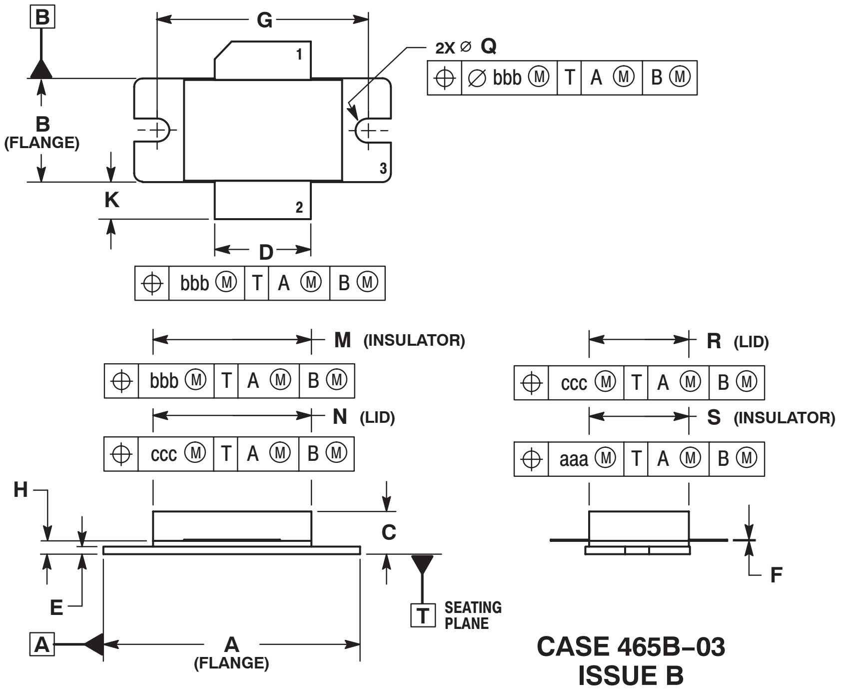


Figure 17. Series Equivalent Source and Load Impedance

NOTES

PACKAGE DIMENSIONS

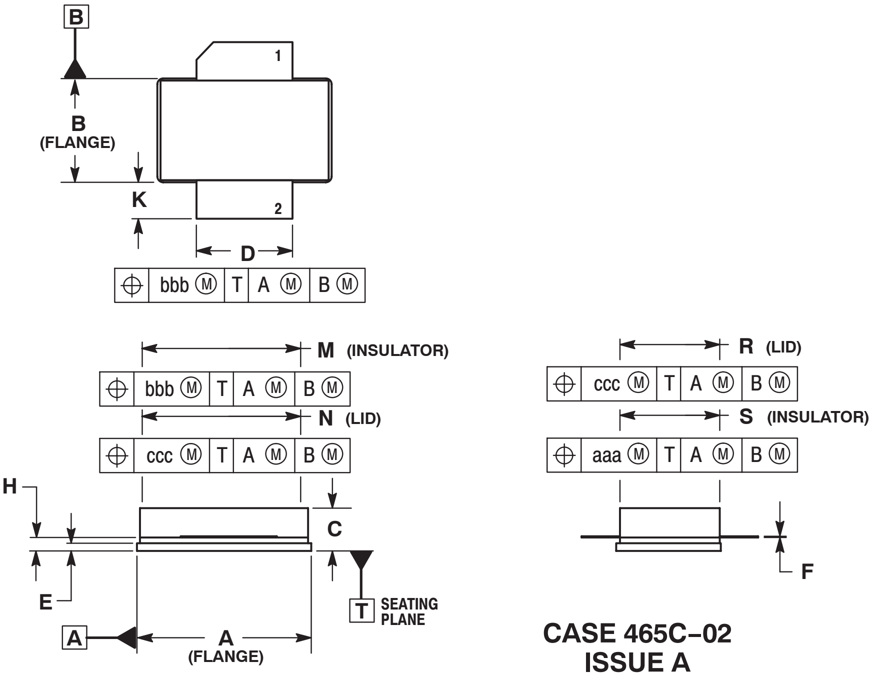


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M−1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
4. DELETED

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	⌀.118	⌀.138	⌀3.00	⌀3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465B−03
ISSUE B
NI−880
MRF9200LR3



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3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.905	0.915	22.99	23.24
B	0.535	0.545	13.60	13.80
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

CASE 465C−02
ISSUE A
NI−880S
MRF9200LSR3

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